

IN THE CLAIMS

Complete listing of the claims

1. (Currently amended) A film forming system comprising:

a chamber,

a precursory gas supplying line to supply the chamber with precursory gas,

a reactive gas supplying line to supply the chamber with reactive gas,

a precursory gas vaporizer for outputting precursory gas to the precursory gas supplying line,

a reactive gas vaporizer for outputting reactive gas to the reactive gas supplying line, and

a purge gas supplying line to supply purge gas that purges the precursory gas and the reactive gas, and that forms a thin film on a substrate in the chamber by supplying the precursory gas or the reactive gas and purging alternately, ~~and~~

wherein the precursory gas supplying line comprises a precursory gas middle line having a predetermined volume that is arranged on a part or all of the precursor supplying line and into which the precursory gas can be filled at a time when the precursory gas is not supplied, and/or
wherein the reactive gas supplying line comprises a reactive gas middle line having a certain volume that is arranged on a part or all of the reactive gas supplying line and into which the reactive gas can be filled at a time when the reactive gas is not supplied,

wherein a first switching valve is provided on the precursory gas supplying line and/or reactive gas supplying line at a position downstream of the precursory gas vaporizer and/or the reactive gas vaporizer at an inlet port of the precursory gas middle line and/or the reactive gas middle line;

wherein a second switching valve is provided on the precursory gas supplying line and/or reactive gas supplying line at a position downstream of the first switching valve at an outlet port of the precursory gas middle line and/or the reactive gas middle line; and

the chamber is provided downstream from the second switching valve.

~~wherein a switching valve is arranged on each of an inlet port and an outlet port of the precursory gas middle line and/or the reactive gas middle line respectively so as to specify a volume of the precursory gas middle line and/or the reactive gas middle line with the~~

~~cross-sectional area of a line body constituting the precursory gas middle line and/or the reactive gas middle line and a distance between each of the switching valves.~~

2. (Cancelled)

3. (Currently amended) The film forming system described in claim 1, wherein the first switching valve or the second switching valve is a three-way valve.

4. (Previously presented) The film forming system described in claim 1, wherein the purge gas supplying line is connected to the precursory gas supplying line to which the precursory gas middle line is arranged and/or the reactive gas supplying line to which the reactive gas middle line is arranged and the precursory gas and/or the reactive gas each of which is filled in the precursory gas middle line and/or the reactive gas middle line is supplied to the chamber by pushing out the precursory gas and/or the reactive gas by the use of the purge gas.

5. (Original) The film forming system described in claim 1, wherein the precursory gas and/or the reactive gas is supplied to the chamber in 0.1 through 2 second.

6. (Previously presented) The film forming system described in claim 1, wherein concentration adjusting devices to adjust each concentration of the precursory gas and the reactive gas is connected to the precursory gas supplying line and the reactive gas supplying line respectively and each concentration adjusting device adjusts each concentration of the precursory gas and the reactive gas so as to supply each gas at more than or equal to 0.15×10^{-6} mol/cm² with respect to an area of the substrate on which the thin film is formed.

7. (Original) The film forming system described in claim 1, wherein each of the precursory gas supplying line and the reactive gas supplying line is independently connected to the chamber.

8. (Original) The film forming system described in claim 1, and that is arranged to purge the

chamber so that each concentration of the precursory gas and/or the reactive gas becomes less than or equal to 1/1000 in less than or equal to 2 seconds.

9. (Cancelled)